NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRAL2023-18** is a Common Base Device Designed for Class C Amplifier Applications in L-Band FM Microwave Links.

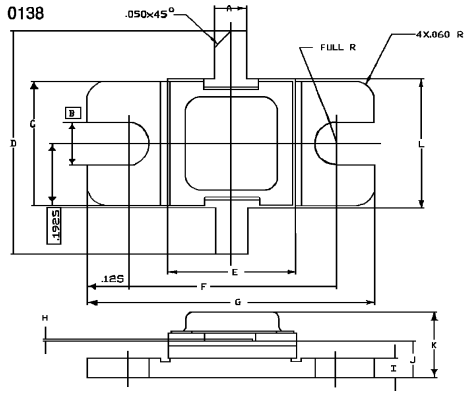
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Input/Output Matching

MAXIMUM RATINGS

I_C	4.0 A
V_{CES}	42 V
P_{DISS}	70 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

PACKAGE STYLE .250 2L FLG (C)



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.095/2.41	.105/2.67
B	0125/3.18	
C	.380/9.65	.390/9.91
D	.780/19.81	
E	.392/9.96	.408/10.36
F	.645/16.38	.655/16.64
G	.895/22.73	.905/22.99
H	.002/0.05	.006/0.15
I	.055/1.40	.065/1.65
J	.105/2.67	.130/3.30
K		.230/5.84
L	.392/.408	.408/10.36

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 160 mA	42			V
BV_{EBO}	I_E = 2.0 mA	3.5			V
I_{CBO}	V_{CB} = 22 V			4.0	mA
h_{FE}	V_{CE} = 5.0 V I_C = 800 mA	10		100	---
P_G	V_{CE} = 22 V f = 2000 - 2300 MHz P_{OUT} = 18.0 W	7.0			dB
η_C		35			%

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Specifications are subject to change without notice.